

40V DUAL NPN SMALL SIGNAL TRANSISTOR IN SOT363

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

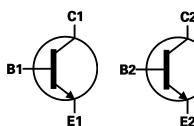
- BV_{CEO} >40V
- I_C = 600mA High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

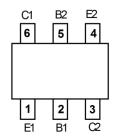
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)

SOT363





Device Symbol



Top View Pin-Out

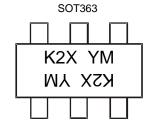
Ordering Information (Note 5)

Product	Compliance	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
MMDT4401Q-7-F	Automotive	K2X	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



$$\begin{split} &\text{K2X} = \text{Product Type Marking Code} \\ &\text{YM} = \text{Date Code Marking} \\ &\text{Y or } \overline{\text{Y}} = \text{Year (ex: E} = 2017)} \\ &\text{M or } \overline{\text{M}} = \text{Month (ex: 9} = \text{September)} \end{split}$$

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	Е		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Z	D



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	Ic	600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	625	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Thermal Characteristic and Derating Information

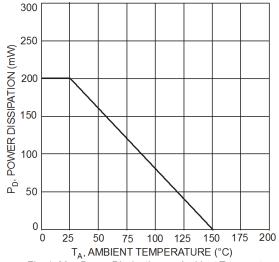


Fig. 1 Max Power Dissipation vs. Ambient Temperature

^{6.} For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

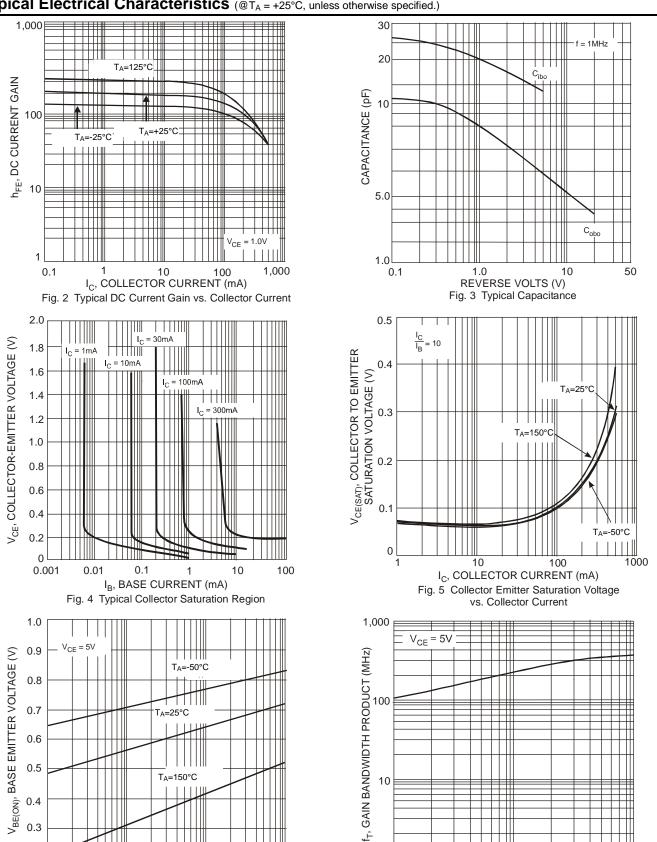
Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	$I_C = 100\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	40	_	V	$I_C = 10.0 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	_	V	$I_E = 100 \mu A, I_C = 0$		
Collector-Emitter Cut-Off Current	I _{CEX}		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$		
Base Cut-Off Current	I _{BL}		100	nA	$V_{CE} = 35V$, $V_{EB(OFF)} = 0.4V$		
ON CHARACTERISTICS (Note 8)							
DC Current Gain	h _{FE}	20 40 80 100 40	 300 	_	$I_C = 100\mu A, V_{CE} = 1.0V$ $I_C = 1.0mA, V_{CE} = 1.0V$ $I_C = 10mA, V_{CE} = 1.0V$ $I_C = 150mA, V_{CE} = 1.0V$ $I_C = 500mA, V_{CE} = 2.0V$		
Collector-Emitter Saturation Voltage	V _{CE} (SAT)	_	0.40 0.75	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.75	0.95 1.2	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}	_	6.5	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$		
Input Capacitance	C_{ibo}	_	30	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$		
Input Impedance	h _{ie}	1.0	15	kΩ			
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$		
Small Signal Current Gain	h _{fe}	40	500	_	f = 1.0kHz		
Output Admittance	h _{oe}	1.0	30	μs			
Current Gain-Bandwidth Product	f⊤	250	_	MHz	$V_{CE} = 30V, I_{C} = 150mA,$ f = 100MHz		
SWITCHING CHARACTERISTICS							
Delay Time	t _D	_	15	ns	$V_{CC} = 30V, I_C = 150mA,$		
Rise Time	t _R	_	20	ns	$V_{BE(OFF)} = 2.0V, I_{B1} = 15mA$		
Storage Time	t _S	_	225	ns	$V_{CC} = 30V, I_C = 150mA,$		
Fall Time	t _F	_	30	ns	$I_{B1} = -I_{B2} = 15\text{mA}$		

Note:

8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



 $\rm I_{C}$, COLLECTOR CURRENT (mA)

Fig. 6 Base Emitter Voltage vs. Collector Current

0.2

100

10 I_C, COLLECTOR CURRENT (mA)

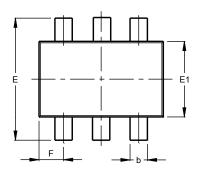
Fig. 7 Gain Bandwidth Product vs. Collector Current

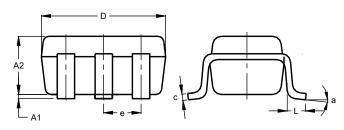


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



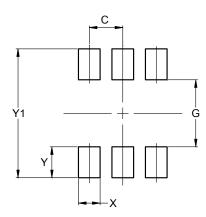


SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.10 0.22 0.11					
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



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